

## 600V, 15A, Trench FS II Fast IGBT

### General Description

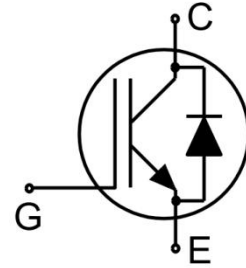
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

### Features

- Trench FSII Technology offering
- Very low  $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in  $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

### Application

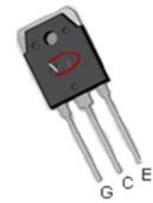
- Air Condition
- Inverters
- Motor drives



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE15TD60BP	TO-3P	NCE15TD60BP



TO-3P

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	30	A
	Collector Current @ $T_C = 100^\circ\text{C}$	15	A
$I_{Cpuls}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	45	A
-	turn off safe operating area, $V_{CE}=600\text{V}$ , $T_j=175^\circ\text{C}$	45	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	15	A
$I_{FM}$	Diode Maximum Forward Current	45	A
$P_D$	Power Dissipation @ $T_C = 25^\circ\text{C}$	105	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	52.5	W
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^\circ\text{C}$
$t_{sc}$	Short circuit withstand time $V_{GE}=15.0\text{V}$ , $V_{CC}\leq 400\text{V}$ , Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}$ , $T_j\leq 150^\circ\text{C}$	5	us

**Thermal Characteristic**

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	1.42	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	2.48	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	$^{\circ}\text{C}/\text{W}$

**Electrical Characteristics ( $T_c=25^{\circ}\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Rating			Units
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0\text{V}, I_{CE}=1\text{mA}$	600	--	--	V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}, V_{CE}=600\text{V}$	--	--	5	$\mu\text{A}$
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30\text{V}, V_{CE}=0\text{V}$	--	--	200	nA
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30\text{V}, V_{CE}=0\text{V}$	--	--	200	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=15\text{A}$ $T_J=25^{\circ}\text{C}$	--	1.7	1.9	V
		$V_{GE}=15\text{V}$ $T_J=175^{\circ}\text{C}$	--	1.9	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1\text{mA}, V_{CE}=V_{GE}$	4.0	--	6.0	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V},$ $f=1\text{MHz}$	--	1635	--	pF
$C_{oes}$	Output Capacitance		--	50	--	
$C_{res}$	Reverse Transfer Capacitance		--	30	--	
$Q_g$	Total Gate Charge	$V_{CC}=480\text{V}, I_C=15\text{A}$ $V_{GE}=15\text{V}$	--	63	--	nC
$Q_{ge}$	Gate to Emitter Charge		--	15	--	
$Q_{gc}$	Gate to Collector Charge		--	26	--	
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0\text{s}$	$V_{GE}=15\text{V}, V_{CC}\leq 400\text{V},$ $t_{sc}\leq 5\mu\text{s}, T_J\leq 150^{\circ}\text{C}$	--	82	--	A
<b>Switching Characteristics</b>						
$t_{d(ON)}$	Turn-on Delay Time	$V_{CC}=400\text{V}, I_C=15\text{A}$ $V_{GE}=0/15\text{V}, R_g=5\Omega$ Inductive Load	--	16	--	ns
$t_r$	Rise Time		--	12	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	124	--	
$t_f$	Fall Time		--	12	--	
$E_{on}$	Turn-On Switching Loss		--	0.25	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	0.12	--	
$E_{ts}$	Total Switching Loss		--	0.37	--	

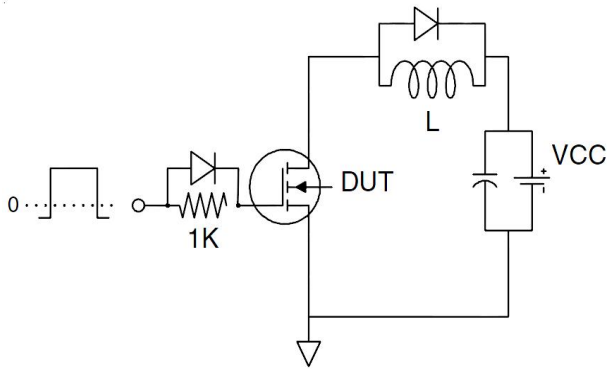
**Electrical Characteristics of the Diode ( $T_c=25^{\circ}\text{C}$  unless otherwise specified)**

Symbol	Parameter	Conditions	Rating			Units
			Min.	Typ.	Max.	
$V_{FM}$	Diode Forward Voltage	$I_F=15\text{A}$	--	1.75	2.40	V
$T_{rr}$	Reverse Recovery Time	$I_F=15\text{A},$ $di/dt=200\text{A}/\mu\text{s}$	--	170	--	ns
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	6.5	--	A
$Q_{rr}$	Reverse Recovery Charge		--	0.6	--	$\mu\text{C}$

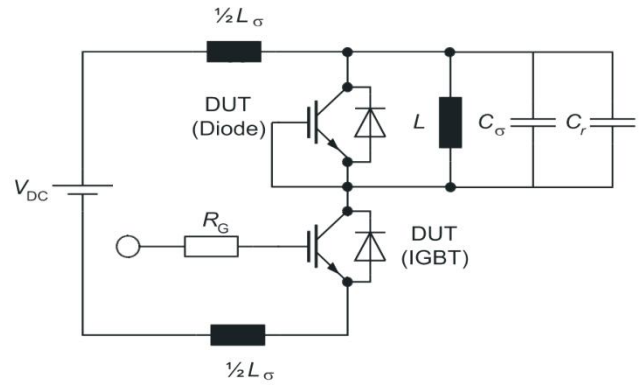
Pulse width  $t_p\leq 380\mu\text{s}, \delta\leq 2\%$

### Test Circuit

#### 1) Gate Charge Test Circuit

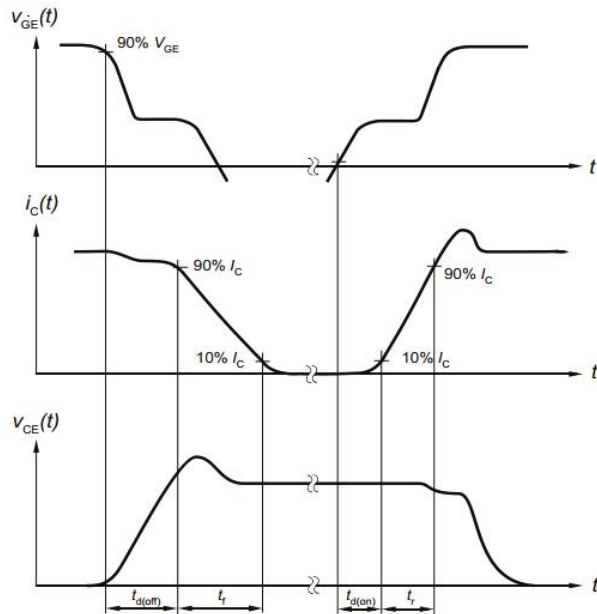


#### 2) Switch Time Test Circuit

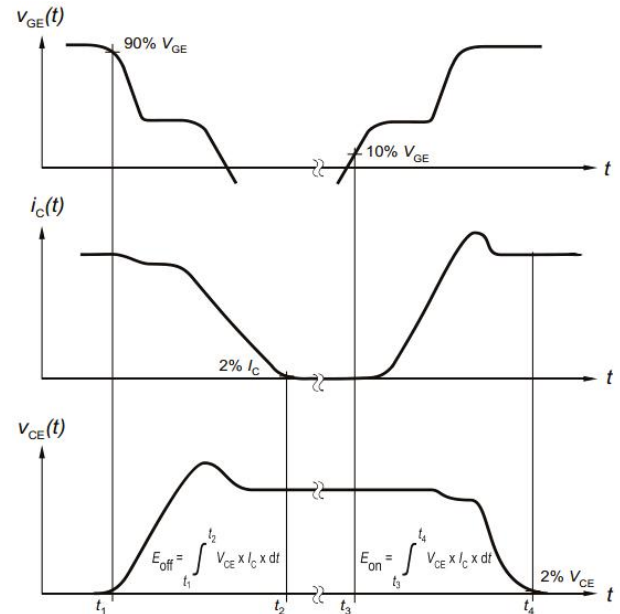


### Switching characteristics

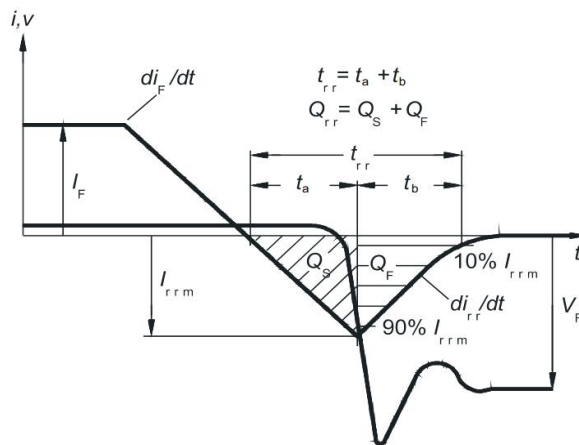
#### 1) Definition of switching times



#### 2) Definition of switching losses



#### 3) Definition of diode switching characteristics



## Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

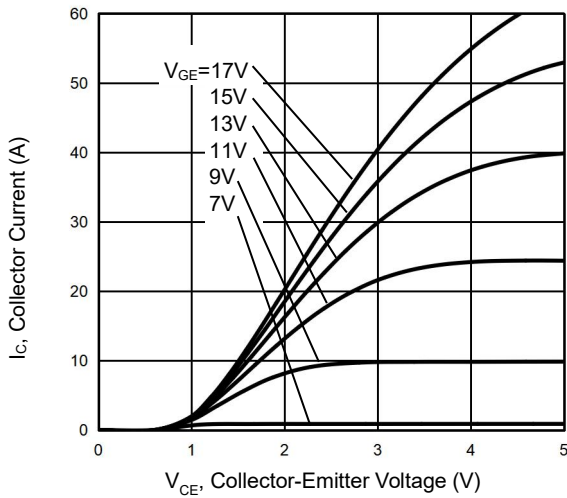


Figure 2 Transfer Characteristics

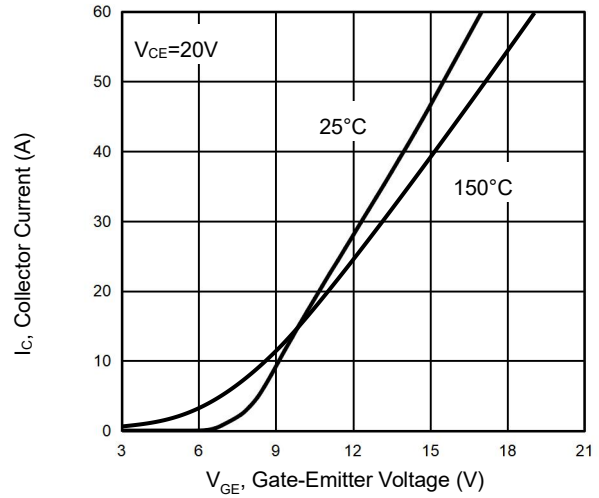


Figure 3  $V_{CEsat}$  vs. Case Temperature

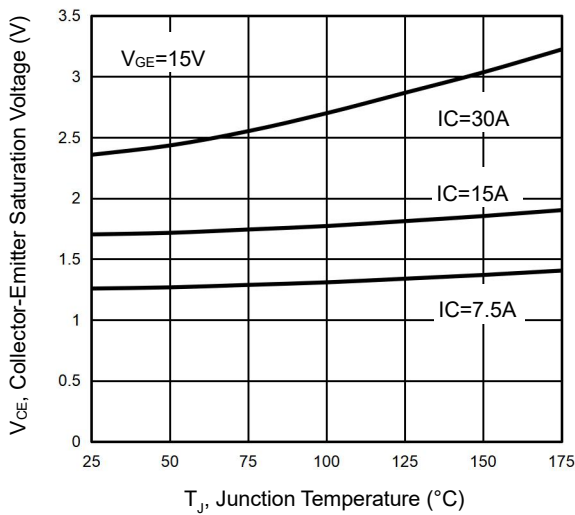


Figure 4 Saturation Voltage vs.  $V_{GE}$

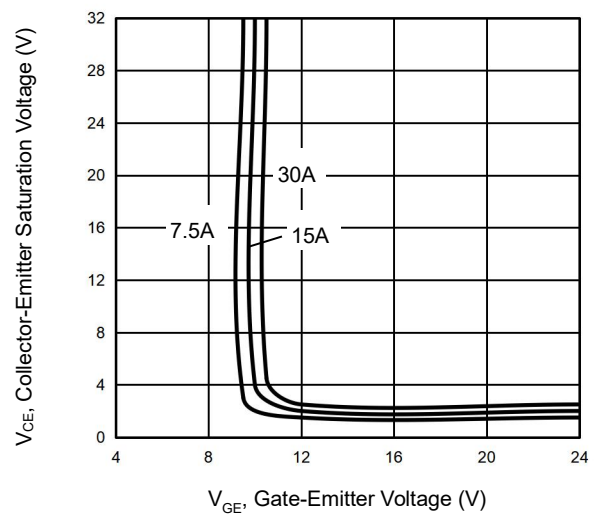


Figure 5 Capacitance Characteristics

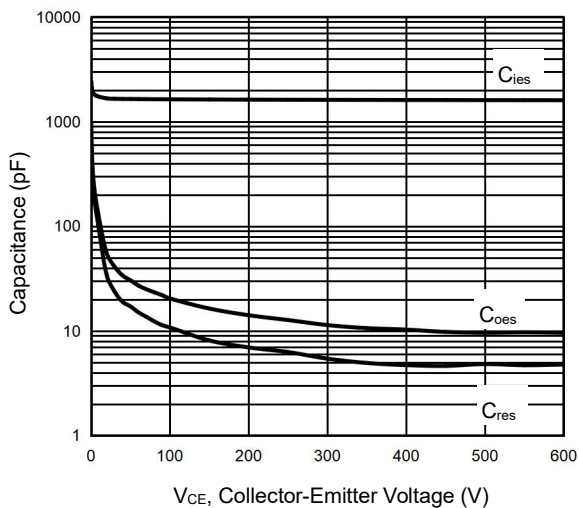
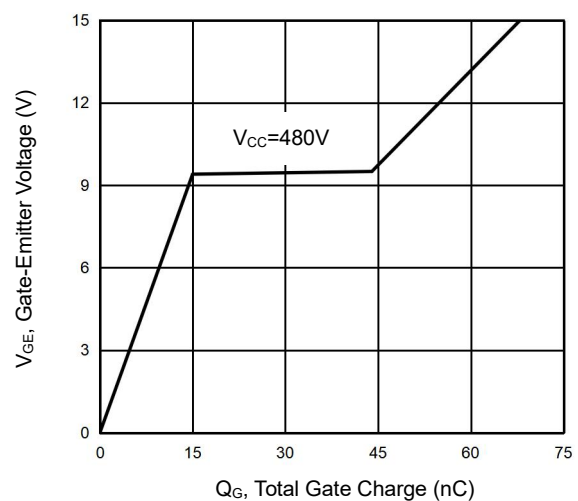


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics

Figure 7 Gate-emitter Threshold Voltage as a Function of Junction Temperature

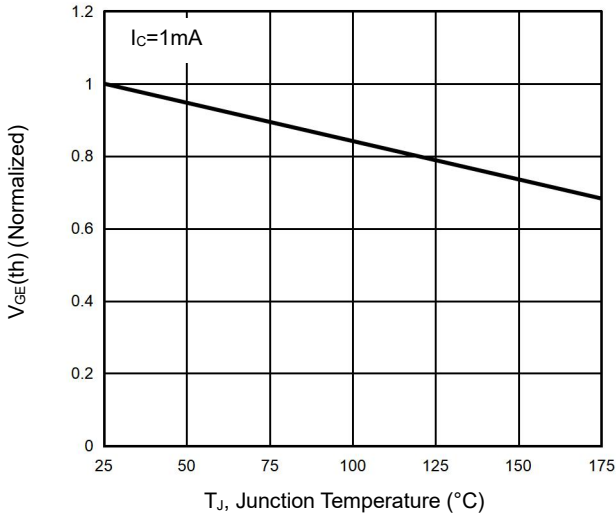


Figure 8 Typical Switching Times as a Function of Gate Resistor

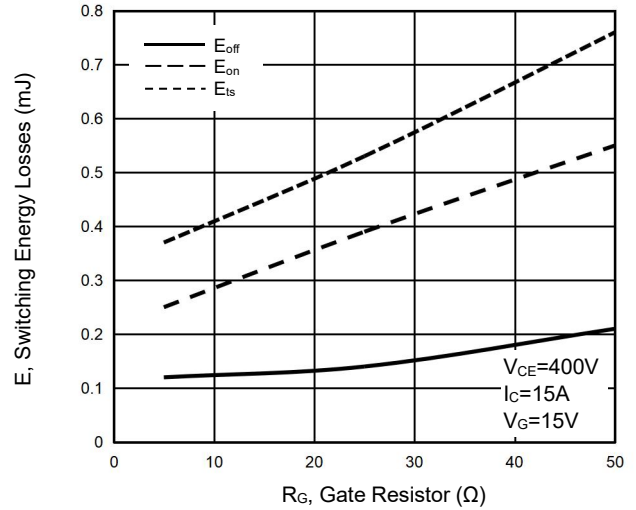


Figure 9 Typical Switching Times as a Function of Junction Temperature

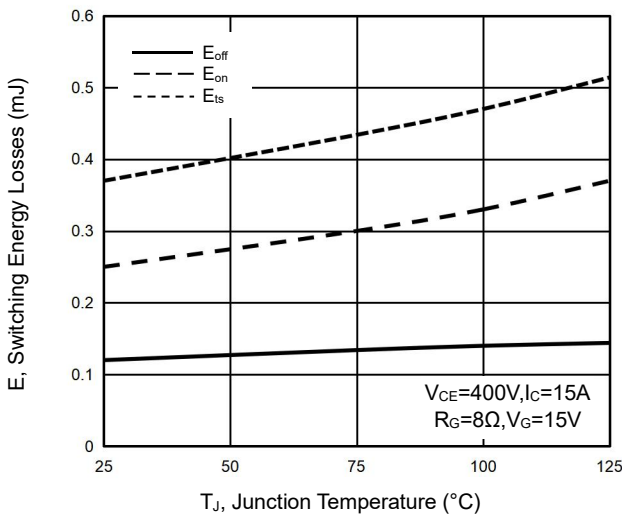


Figure 10 Power Dissipation as a Function of Case Temperature

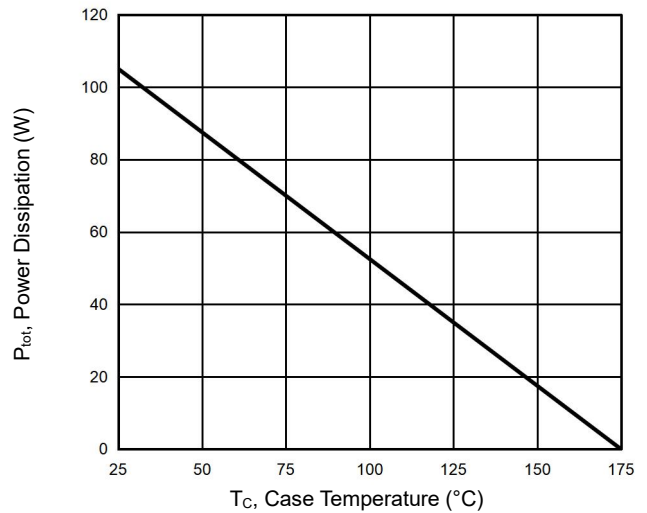


Figure 11 Forward Bias Safe Operating

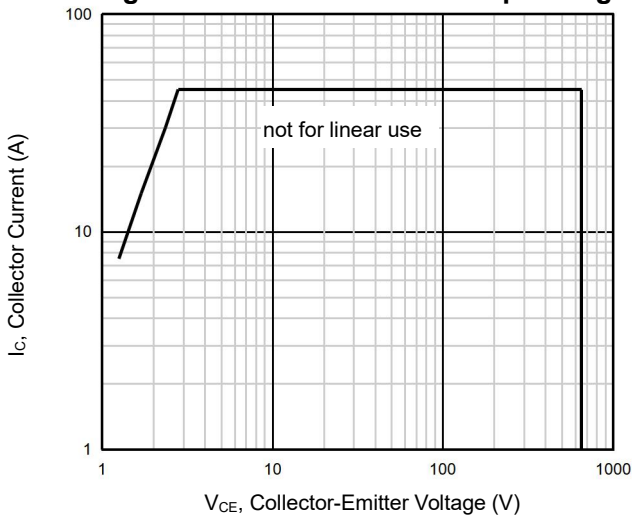
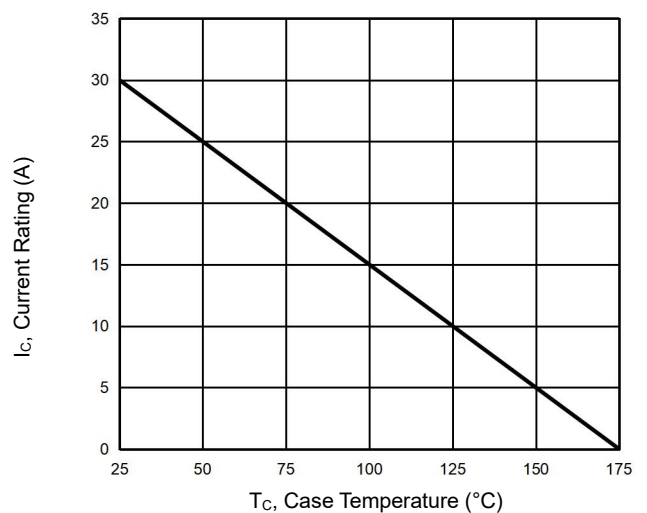


Figure 12 IC vs. Temperature



Typical Electrical and Thermal Characteristics

Figure 13 Forward Characteristics

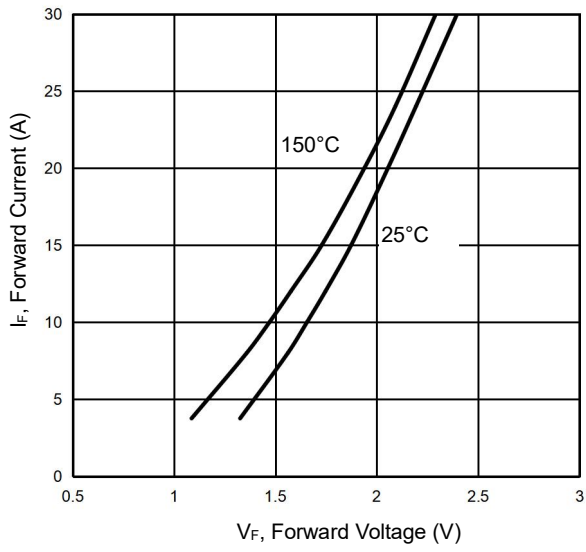
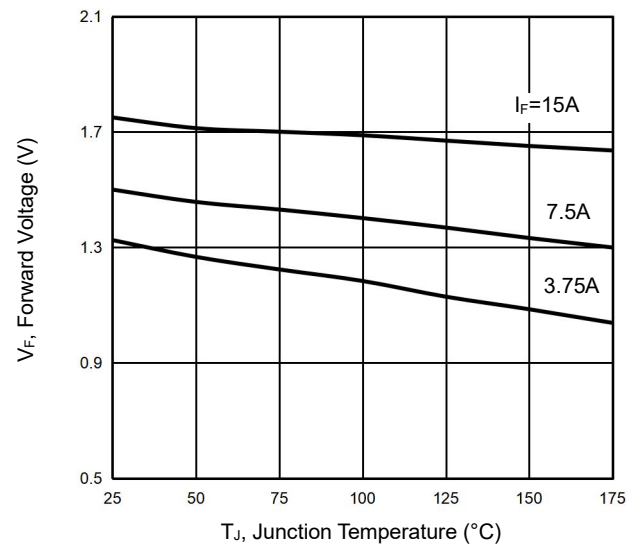
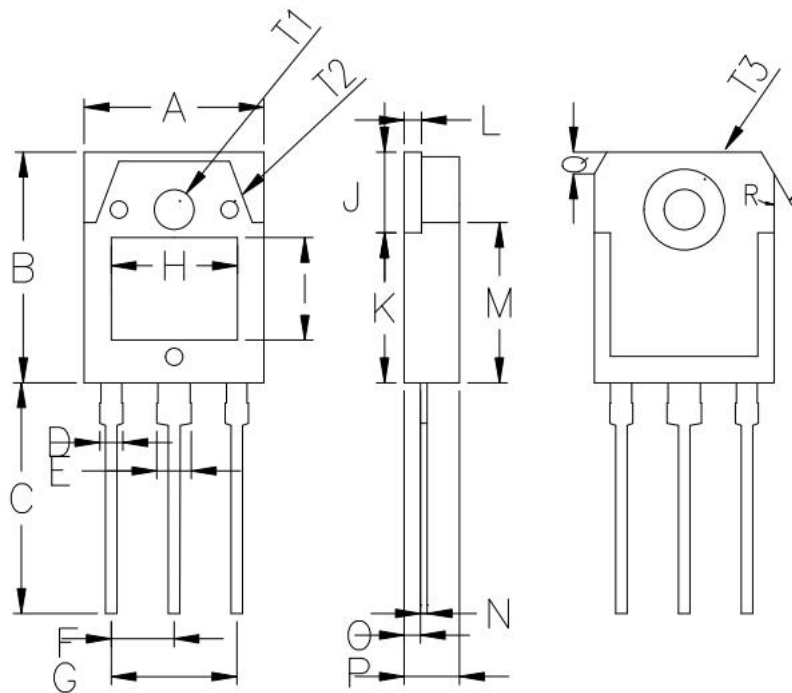


Figure 14  $V_F$  vs. Temperature



## TO-3P-S Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.50	15.70	0.61	0.62
B	19.70	20.10	0.78	0.79
C	20.10	20.50	0.79	0.81
D	2.00		0.08	
E	3.00		0.12	
F	5.45		0.21	
G	10.90		0.43	
H	10.80	11.00	0.43	0.43
I	8.80	9.00	0.35	0.35
J	6.85	7.15	0.27	0.28
K	12.75	13.05	0.50	0.51
L	1.49	1.51	0.06	0.06
M	13.70	14.00	0.54	0.55
N	0.59	0.61	0.02	0.02
O	1.32	1.48	0.05	0.06
P	4.70	4.90	0.19	0.19
Q	1.90	2.10	0.07	0.08
R	30°		30°	
S	4°		4°	
T1	3.50		0.14	
T2	1.50		0.06	
T3	7.00		0.28	

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